

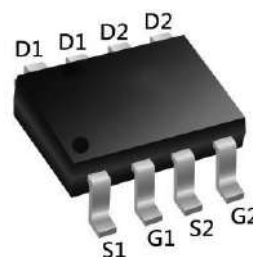
Dual N-Ch 100V Fast Switching MOSFETs

Features:

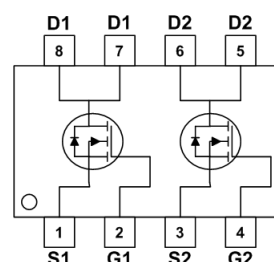
- ★ Super Low Gate Charge
- ★ Green Device Available
- ★ Excellent Cdv/dt effect decline
- ★ Advanced high cell density Trench technology

Description:

The KSCS0228 is the high cell density trenched N-ch MOSFETs, which provides excellent RDSON and efficiency for most of the small power switching and load switch applications. The KSCS0228 meets the RoHS and Green Product requirement with full function reliability approved.



SOP8 Pin Configuration



Product Summary

BVDSS	RDSON	ID
100V	68mΩ	4A

Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	100	V
V_{GS}	Gate-Source Voltage	±20	V
$I_D@T_A=25^{\circ}C$	Continuous Drain Current, V_{GS} @ 10V ¹	4	A
$I_D@T_A=70^{\circ}C$	Continuous Drain Current, V_{GS} @ 10V ¹	3	A
I_{DM}	Pulsed Drain Current ²	25	A
EAS	Single Pulse Avalanche Energy ³	0.8	mJ
I_{AS}	Avalanche Current	4	A
$P_D@T_A=25^{\circ}C$	Total Power Dissipation ⁴	2	W
$P_D@T_A=70^{\circ}C$	Total Power Dissipation ⁴	1.3	W
T_{STG}	Storage Temperature Range	-55 to 150	°C
T_J	Operating Junction Temperature Range	-55 to 150	°C

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient ¹	---	90	°C/W
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	40	°C/W

Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	100	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance ²	$V_{GS}=10V, I_D=4A$	---	---	68	$m\Omega$
		$V_{GS}=4.5V, I_D=3A$	---	---	94	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}, I_D=250\mu A$	1.5	---	2.9	V
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=80V, V_{GS}=0V, T_J=25^\circ\text{C}$	---	---	10	μA
		$V_{DS}=80V, V_{GS}=0V, T_J=55^\circ\text{C}$	---	---	100	
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	---	---	± 100	nA
g_{fs}	Forward Transconductance	$V_{DS}=5V, I_D=4A$	---	14	---	S
R_g	Gate Resistance	$V_{DS}=0V, V_{GS}=0V, f=1\text{MHz}$	---	3	---	Ω
Q_g	Total Gate Charge (10V)	$V_{DS}=50V, V_{GS}=10V, I_D=4A$	---	11.9	---	nC
Q_{gs}	Gate-Source Charge		---	2.6	---	
Q_{gd}	Gate-Drain Charge		---	1.7	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=50V, V_{GS}=10V, R_G=3\Omega$ $I_D=4A$	---	3.8	---	ns
T_r	Rise Time		---	25.8	---	
$T_{d(off)}$	Turn-Off Delay Time		---	16	---	
T_f	Fall Time		---	8.8	---	
C_{iss}	Input Capacitance	$V_{DS}=25V, V_{GS}=0V, f=1\text{MHz}$	---	620	---	pF
C_{oss}	Output Capacitance		---	105	---	
C_{rss}	Reverse Transfer Capacitance		---	63	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current ^{1,5}	$V_G=V_D=0V$, Force Current	---	---	2.5	A
V_{SD}	Diode Forward Voltage ²	$V_{GS}=0V, I_S=1A, T_J=25^\circ\text{C}$	---	---	1.2	V
t_{rr}	Reverse Recovery Time	$I_F=4A, dI/dt=100A/\mu s, T_J=25^\circ\text{C}$	---	30	---	nS
Q_{rr}	Reverse Recovery Charge		---	37	---	nC

Note :

1.The data tested by surface mounted on a 1 inch² FR-4 board with 20Z copper.

2.The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$

3.The EAS data shows Max. rating . The test condition is $V_{DD}=25V, V_{GS}=10V, L=0.1mH, I_{AS}=4A$

4.The power dissipation is limited by 150°C junction temperature

5.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.